

December 2013

FQN1N60C

N-Channel QFET® MOSFET

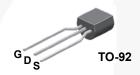
600 V, 0.30 A, 11.5 Ω

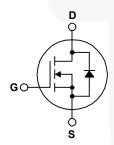
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 0.30 A, 600 V, $R_{DS(on)}$ = 11.5 Ω (Max.) @ V_{GS} = 10 V, I_D = 0.15 A
- Low Gate Charge (Typ. 4.8 nC)
- Low Crss (Typ. 3.5 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	ol Parameter		FQN1N60CTA	Unit
V _{DSS}	Drain-Source Voltage		600	V
I _D	Drain Current - Continuous (T _C = 25°C)		0.3	A
	- Continuous (T _C = 100°C)		0.18	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	1.2	A
V_{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		33	mJ
I _{AR}	Avalanche Current (Note 1)		0.3	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		0.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_{D}	Power Dissipation (T _A = 25°C)		1	W
	Power Dissipation (T _L = 25°C)		3	W
	- Derate above 25°C		0.02	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C

Thermal Characteristics

Symbol	Parameter	FQN1N60CTA	Unit	
$R_{ heta JL}$	Thermal Resistance, Junction-to-Lead, Max.	(Note 5a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max. (Note 5b)		140	- 0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQN1N60CTA	1N60C	TO-92	AMMO	N/A	N/A	2000 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Characte	ristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.6		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V			50	μΑ
		V _{DS} = 480 V, T _C = 125°C			250	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$	/ -		-100	nA
On Characte	ristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.15 A	-	9.3	11.5	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 0.3 A	\	0.75		S
Dynamic Cha	aracteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		130	170	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		19	25	pF
C _{rss}	Reverse Transfer Capacitance		1	3.5	6	pF
Switching Ch	naracteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 1.1 A,		7	24	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		21	52	ns
t _{d(off)}	Turn-Off Delay Time			13	36	ns
t _f	Turn-Off Fall Time	(Note 4)	-/	27	64	ns
Qg	Total Gate Charge	V _{DS} = 480 V, I _D = 1.1 A,	-	4.8	6.2	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	1	0.7	/-	nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	2.7		nC
Drain-Source	Diode Characteristics and Maximum R	atings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				0.3	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-		1.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.3 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 1.1 A,	-	190		ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		0.53		μС

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 59 mH, I $_{AS}$ = 1.1 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- $3.~I_{SD} \leq 0.3~A,~di/dt \leq 200~A/\mu s,~V_{DD} \leq BV_{DSS,}~starting~~T_J = 25^{\circ}C.$
- 4. Essentially independent of operating temperature.

- 5. a) Reference point of the R_{B,IL} is the drain lead.
 b) When mounted on 3"x4.5" FR-4 PCB without any pad copper in a still air environment (R_{B,IA} is the sum of the junction-to-case and case-to-ambient thermal resistance. R_{BCA} is determined by the user's board design)

Typical Performance Characteristics

Figure 1. On-Region Characteristics

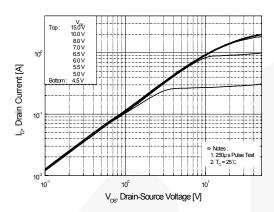


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

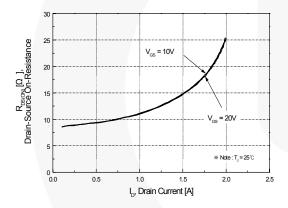


Figure 5. Capacitance Characteristics

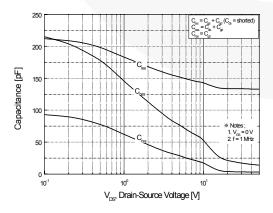


Figure 2. Transfer Characteristics

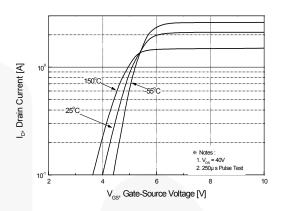


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

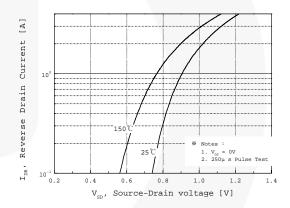
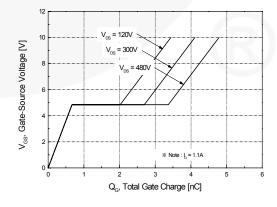


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

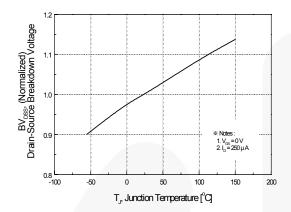


Figure 9. Maximum Safe Operating Area

Figure 8. On-Resistance Variation vs. Temperature

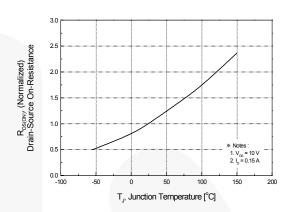
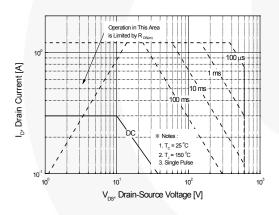


Figure 10. Maximum Drain Current vs. Case Temperature



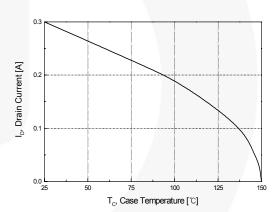
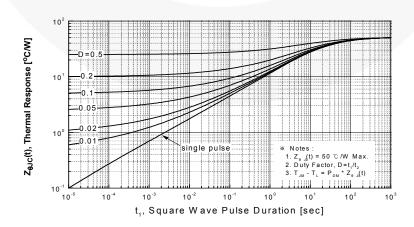


Figure 11. Transient Thermal Response Curve



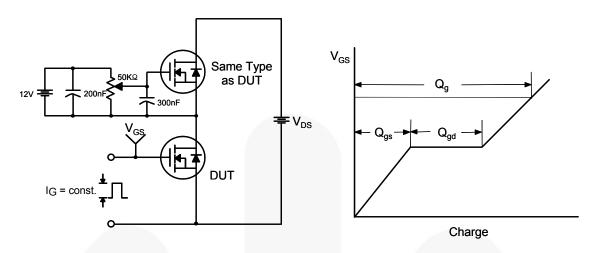


Figure 12. Gate Charge Test Circuit & Waveform

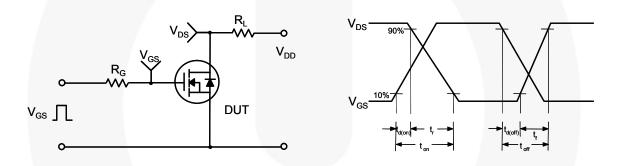


Figure 13. Resistive Switching Test Circuit & Waveforms

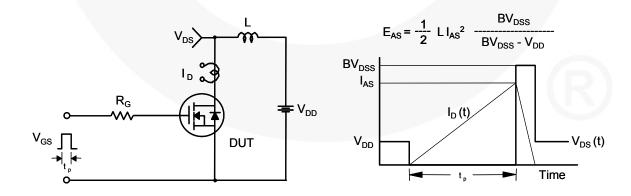


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

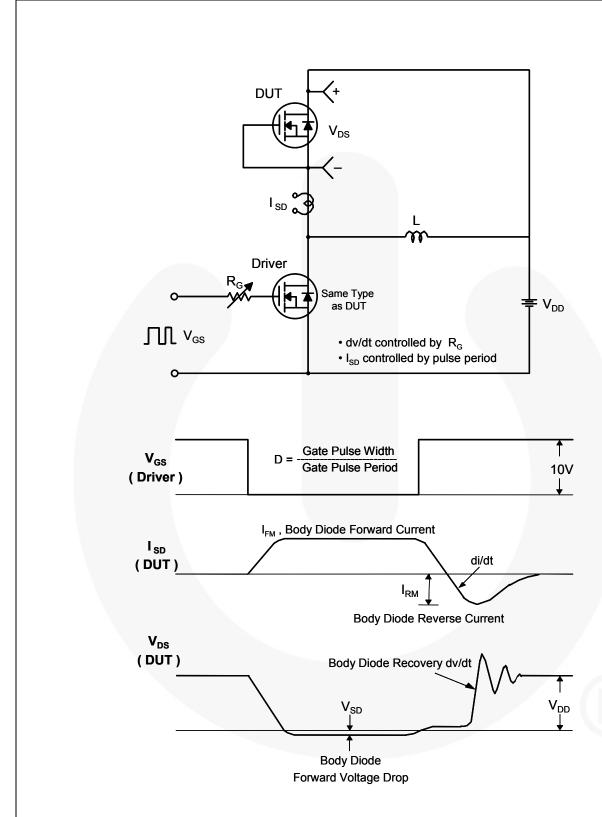


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

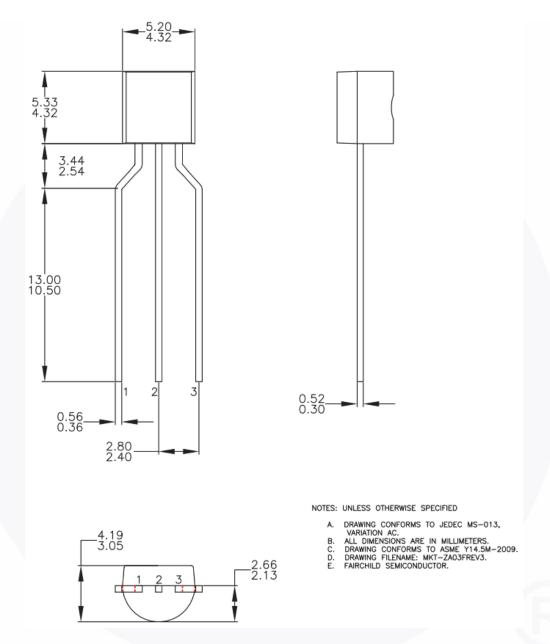


Figure 16. TO92, Molded, 3-Lead, 0.200 In Line Spacing LD Form (J61Z Option)

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